Call for Paper – special session on GaN Based Devices and Circuits for 5G Technology



5G technology is the next platform to provide higher speed, better range and reliable wireless connectivity. Among several matured candidates, GaN offer the highest Johnson figure of merit - a measure of semiconductor applicability for high frequency applications. Thus, a special session will be organized during TENCON 2019 to highlight the advancement of GaN devices and circuits for 5G applications. Papers are invited for submission under the following topics (not limited):

□ GaN HEMTs: advances in growth, passivation, contact, device design and modelling schemes.

- □ Long term reliability assessment of GaN HEMTs.
- Advances in GaN HEMT circuits: power amplifiers, low noise amplifiers, phase shifters, etc.
- □ Application of GaN HEMT in Monolithic Microwave Integrated Circuits (MMICs).

Authors are invited to submit full paper (Maximum 6 pages, double- column US letter size) as PDF using the IEEE templates. The submission can done through the TENCON website <u>www.tencon2019.org</u>.

Submission Deadline: June 30, 2019 Paper Notification date: August 15, 2019 Camera-Ready: August 30, 2019 Session Organizer: Biplab Sarkar Co-organizers: Karun Rawat, Darshak Bhatt Affiliation: Dept. of ECE, IIT Roorkee